



List of Publications

- 1 “Growth of high quality silicon nitride films in low power nitrogen plasma at temperatures below 300°C” K. Nauka, E. C. Paloura, J. Lagowski and H. C. Gatos, Extended Abstracts, Electrochemical Society Fall Meeting, Las Vegas, **85-2**, 390 (1985).
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- 4 “Low temperature plasma growth of thin Si_3N_4 films and characterization of the Si_3N_y -Si interface” E. C. Paloura, J. Lagowski and H. C. Gatos, Proc. 20th International Conference on the Physics of Semiconductors, p. 336, Ed. E. M. Anastasakis and J. D. Joannopoulos, World Scientific (1990).
- 5 “Growth and electronic properties of thin Si_3N_4 films grown on Si in a nitrogen glow discharge”, E. C. Paloura, J. Lagowski and H. C. Gatos, J. Appl. Phys. **69**, 3995 (1991).
- 6 “New application for isothermal capacitance transient spectroscopy: Identification of tunneling in semiconductor-insulator interfaces”, E. C. Paloura, J. Lagowski and H. C. Gatos, Appl. Phys. Lett. **58**, 137 (1991).
- 7 “Deep level analysis of lattice-matched $\text{Ga}_x\text{In}_{1-x}\text{P}/\text{GaAs}$ heterojunctions grown by MOMBE and MOVPE” E. C. Paloura, A. Ginoudi, G. Constandinidis and G. Kiriakidis, Proc., 1st Conf. of the Balkan Physical Union, p.1014 (1991).
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- 10 “Effect of doping on electron traps in metalorganic molecular-beam epitaxial $\text{Ga}_x\text{In}_{1-x}\text{P}/\text{GaAs}$ heterostructures” E. C. Paloura, A. Ginoudi, G. Kiriakidis and A. Christou, Appl. Phys. Lett. **59**, 3127 (1991).
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- 13 “On the contribution of a nitrogen-related defect in the NEXAFS spectra of thin Si_3N_4 films” E. C. Paloura, A. Knop, U. Döbler, K. Holldack and S. Logothetidis, Proc. Fall MRS Symposium, Vol.**284**, p. 107 (1992).

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- 15 **“X-Ray absorption studies of nitrogen implanted into Si and bombarded SiN layers”** K. Holldack, H. Kerkow, A. Mertens, U. Döbler, A. Knop, E. Paloura, 8th Int. Conf. on "Ion Beam Modification of Materials", Sept. 1992, Heidelberg, Germany.
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- 18 **“On the identification of N-dangling bonds in SiN films using X-ray absorption studies”** E. C. Paloura, A. Knop, K. Holldack, U. Döbler and S. Logothetidis, J. Appl. Phys. **73**, 2995 (1993).
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- 25 **“Characterization of buried SiN_x films with EXAFS and NEXAFS”** E. C. Paloura, A. Mertens, W. Frentrup, U. Döbler, A. Knop and W. Braun, Physica B **208&209**, 509 (1995).
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- 32 **“Microstructural characterization of stoichiometric buried Si₃N₄ films”** E. C. Paloura, A. Ginoudi, A. Markwitz, Ch. Lioutas, M. Katsikini, K. Bethge, S. Aminpirooz, H. Rossner, E. Holub-Krappe, T. Zorba, D. Siapkias, Nucl. Instr. & Methods B **113**, 227 (1996).
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Last update: Jan. 2011